Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	88148	MRAM or ((magnetoresistive or (magneto-resistive) or magnetic) near3 memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/25 10:16
L2	14237	1 and (method near4 (manufactur\$3 or form\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/25 10:18
L3	128	2 and toroidal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/25 10:18
L4	14453	1 and (method near4 (manufactur\$3 or form\$3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/25 10:18
L5	174	4 and toroidal	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/07/25 10:18
L6	107	5 and @ad<"20030328"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/25 10:19
S1	72	ezaki-joichiro.in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/23 17:26

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S2	143	koga-keiji.in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/23 17:26
S3	110	kakinuma-yuji.in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/23 17:27
S4	1	((magnetic adj memory adj cell) and (stacked adj bodies) and (magneto-sensitive adj layer) and (magnetization adj direction near9 changes) and (external adj magnetic adj field) and (direction adj perpendicular) and (toroidal adj magnetic adj layer)).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/23 17:30
S5	10583	MRAM or (magnetic adj cell)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/23 17:31
S6	22	S5 and (magneto-sensitive adj layer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/23 17:31
S7	1635	(magneto-sensitive or magnetosensitive)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/23 17:32
S8	42	S5 and S7	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/23 17:32

S9	5	S8 and toroidal	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/24 13:53
S10		S9 and @ad<"20030328"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/24 13:54
S11	581	toroidal with stack\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/23 17:45
S12	10	S5 and S11	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/23 17:33
S13	0	S12 and @ad<"20030328"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2007/07/23 17:34
S14	344	S11 and @ad<"20030328"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/23 17:37
S15	149	S14 and magnetic	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/23 17:34

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S16	150	S14 and magneti\$6	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/23 17:42
S17	38	S16 and perpendicular	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2007/07/23 17:40
S18	3	S17 and memory	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/23 17:36
S19	28	MRAM and toroidal	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/23 17:46
S20	14	S19 and @ad<"20030328"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/25 10:19
S21	70	S14 and perpendicular	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/23 17:40
S22	38	S21 and magneti\$6	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/23 17:43

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S23	3	S22 and memory	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/23 17:45
S24	88042	MRAM or ((magnetoresistive or (magneto-resistive) or magnetic) near3 memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/23 17:45
S25	24	S24 and (toroidal with stack\$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/23 17:45
S26	4	S25 and @ad<"20030328"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/23 17:46
S27	2705	365/158	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/23 17:49
S28	31	S27 and toroidal	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/23 17:49
S29	. 18	S28 and @ad<"20030328"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/23 17:49

S30	1976	365/171	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/23 17:50
S31	26	S30 and toroidal	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/23 17:51
S32	16	S31 and @ad<"20030328"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/23 17:51
533	1697	365/173	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/23 17:50
S34	17	S33 and toroidal	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/23 17:51
S35	13	S34 and @ad<"20030328"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/23 17:51
S36	88148	MRAM or ((magnetoresistive or (magneto-resistive) or magnetic) near3 memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/24 13:53

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S37	826	S36 and toroidal	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/24 13:53
S38	251	S37 and @ad<"20030328"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON ·	2007/07/24 13:54
S39	100	S38 and stack\$2	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2007/07/24 13:55